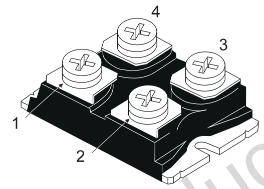
STE70NM50

N-CHANNEL 500V - 0.045Ω - 70A ISOTOP
Zener-Protected MDmesh™Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STE70NM50	500V	< 0.05Ω	70 A

- TYPICAL R_{DS}(on) = 0.045Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL
- INDUSTRY’S LOWEST ON-RESISTANCE



ISOTOP

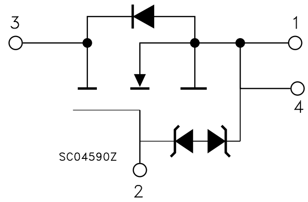
DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company’s PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company’s proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition’s products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	500	V
V_{GS}	Gate- source Voltage	±30	V
I_D	Drain Current (continuous) at T_C = 25°C	70	A
I_D	Drain Current (continuous) at T_C = 100°C	44	A
I_{DM} (•)	Drain Current (pulsed)	280	A
P_{TOT}	Total Dissipation at T_C = 25°C	600	W
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=15KΩ)	6	KV
	Derating Factor	5	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15	V/ns
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤60A, di/dt ≤400A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_j \le T_{JMAX}$

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.2	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	30	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 35 V)	1.4	J

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	500			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			10	µA
		V_{DS} = Max Rating, T_C = 125 °C			100	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			± 10	µA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 30A		0.045	0.05	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 30A		35		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		7500		pF
C_{oss}	Output Capacitance			980		pF
C_{rss}	Reverse Transfer Capacitance			200		pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.5		Ω

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 250V, I_D = 30A R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		51 58		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400V, I_D = 60A, V_{GS} = 10V		190 53 97	266	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 400V, I_D = 60A, R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		51 46 108		ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				60 240	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 60A, V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 60A, di/dt = 100A/µs, V_{DD} = 100 V, T_j = 25°C (see test circuit, Figure 5)		532 9.9 37		ns µC A
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 60A, di/dt = 100A/µs, V_{DD} = 100 V, T_j = 150°C (see test circuit, Figure 5)		636 13.4 42		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

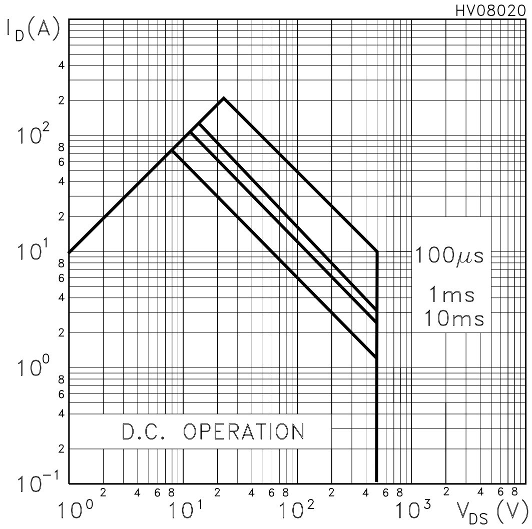
GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	30			V

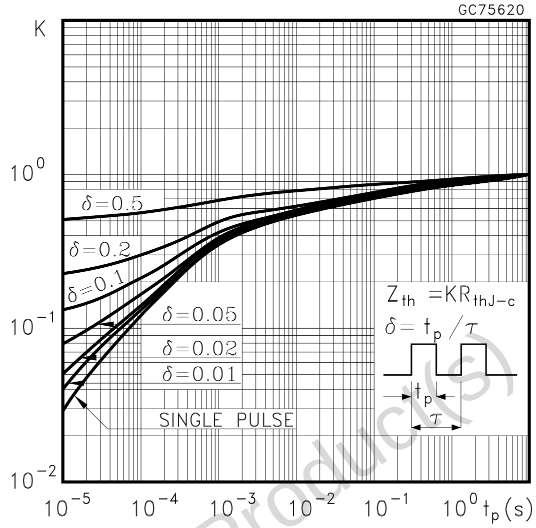
PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the 25V Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

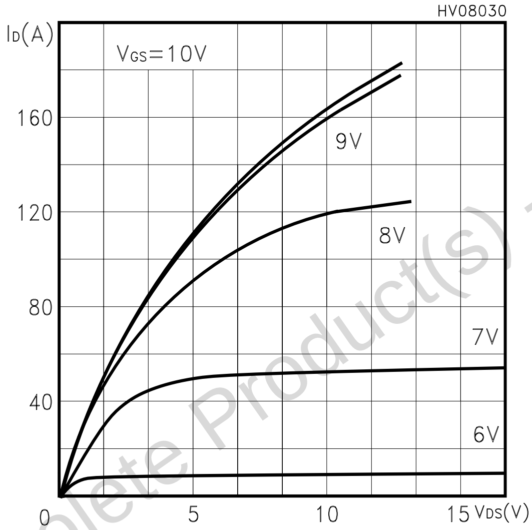
Safe Operating Area



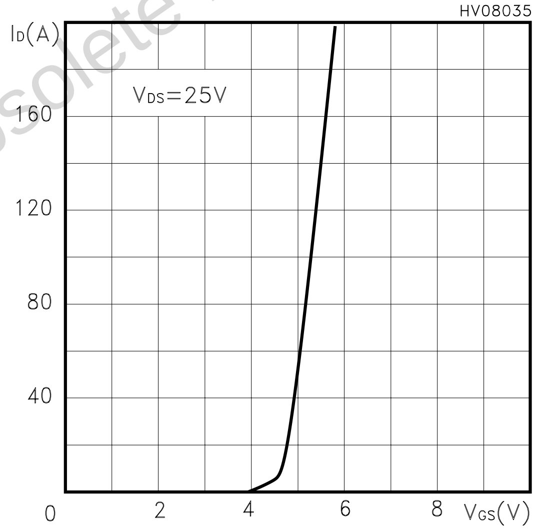
Thermal Impedance



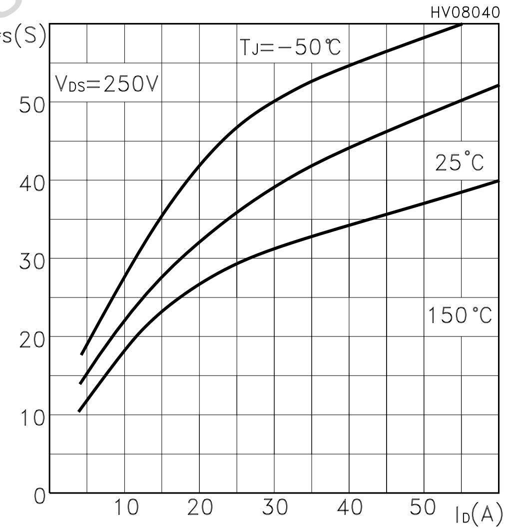
Output Characteristics



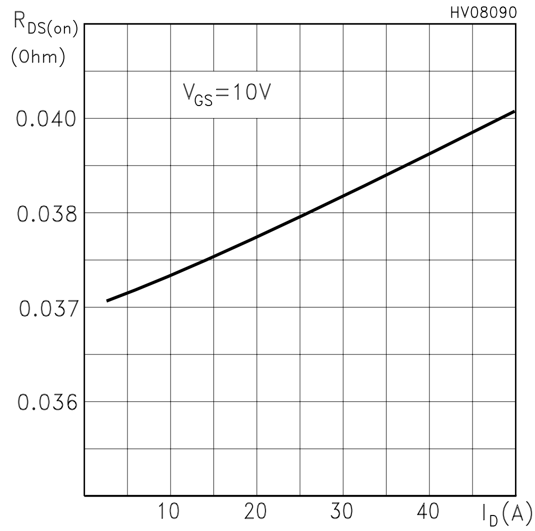
Transfer Characteristics



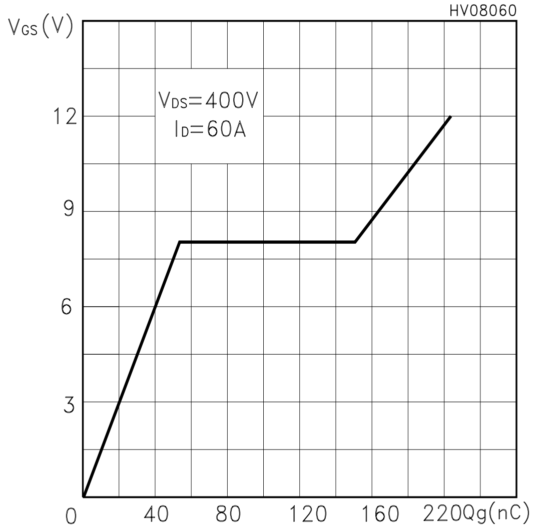
Transconductance



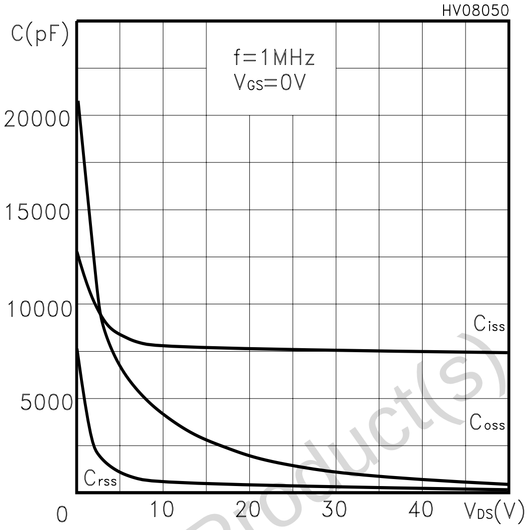
Static Drain-source On Resistance



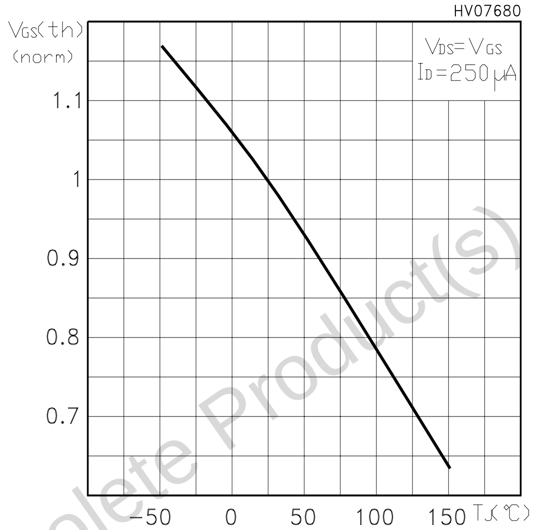
Gate Charge vs Gate-source Voltage



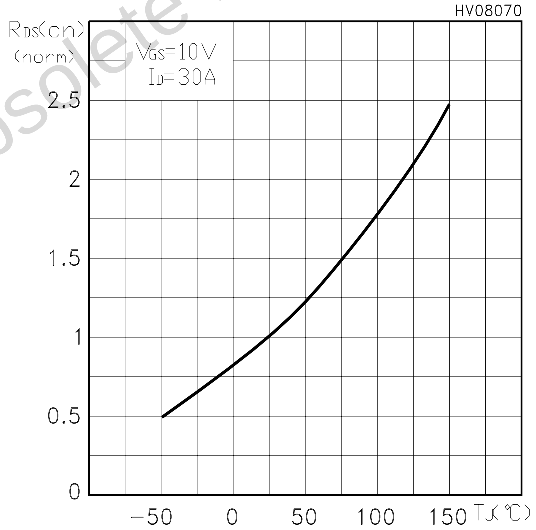
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

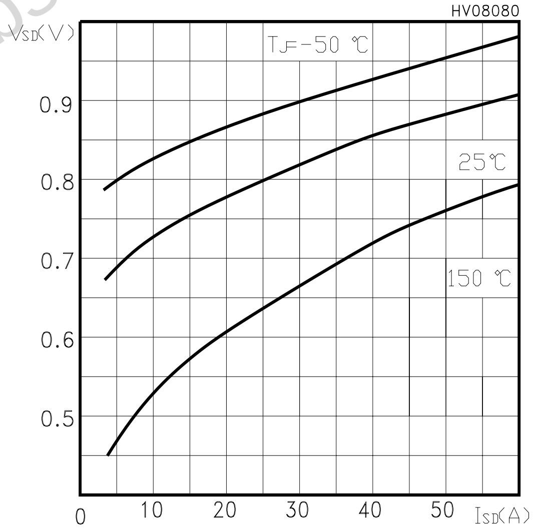


Fig. 1: Unclamped Inductive Load Test Circuit

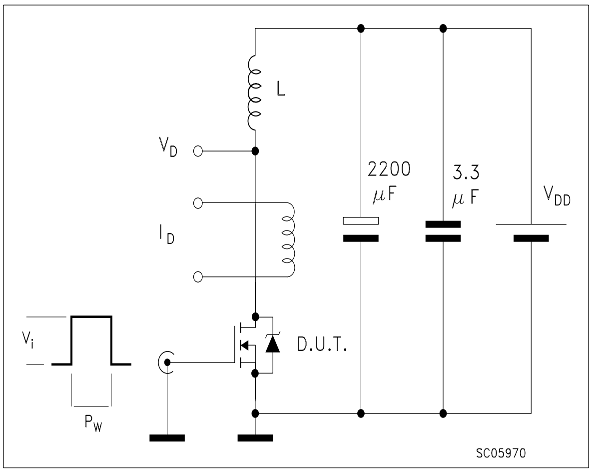


Fig. 2: Unclamped Inductive Waveform

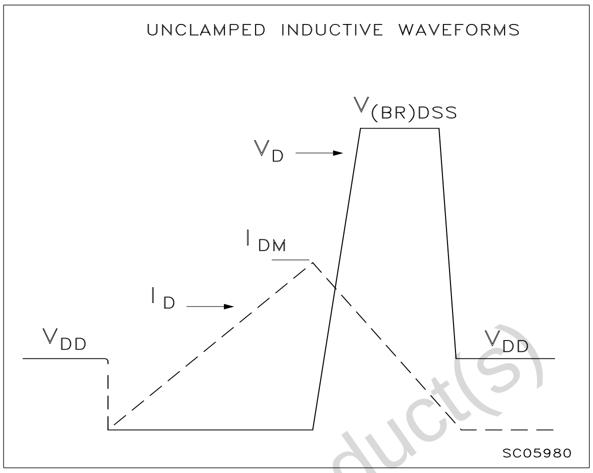


Fig. 3: Switching Times Test Circuit For Resistive Load

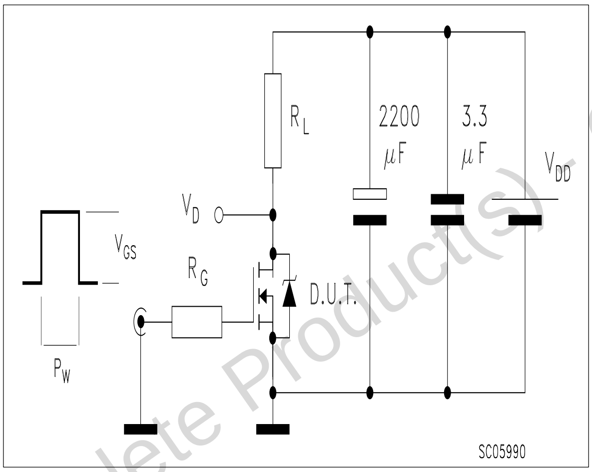


Fig. 4: Gate Charge test Circuit

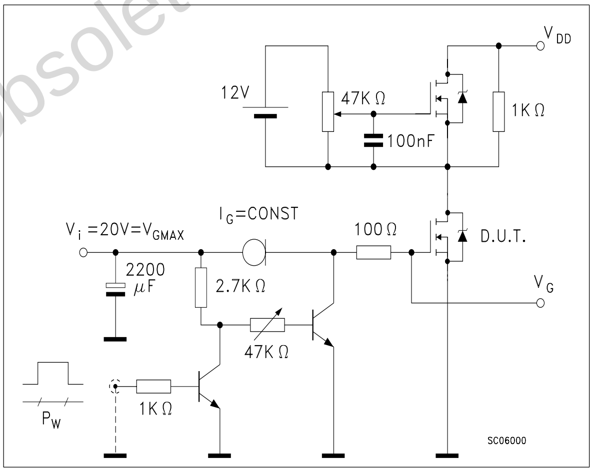
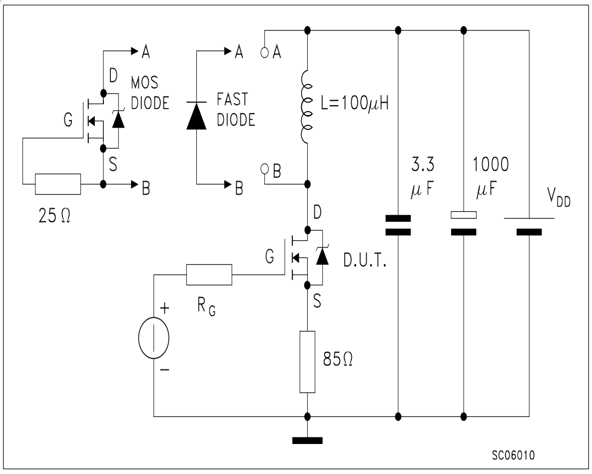
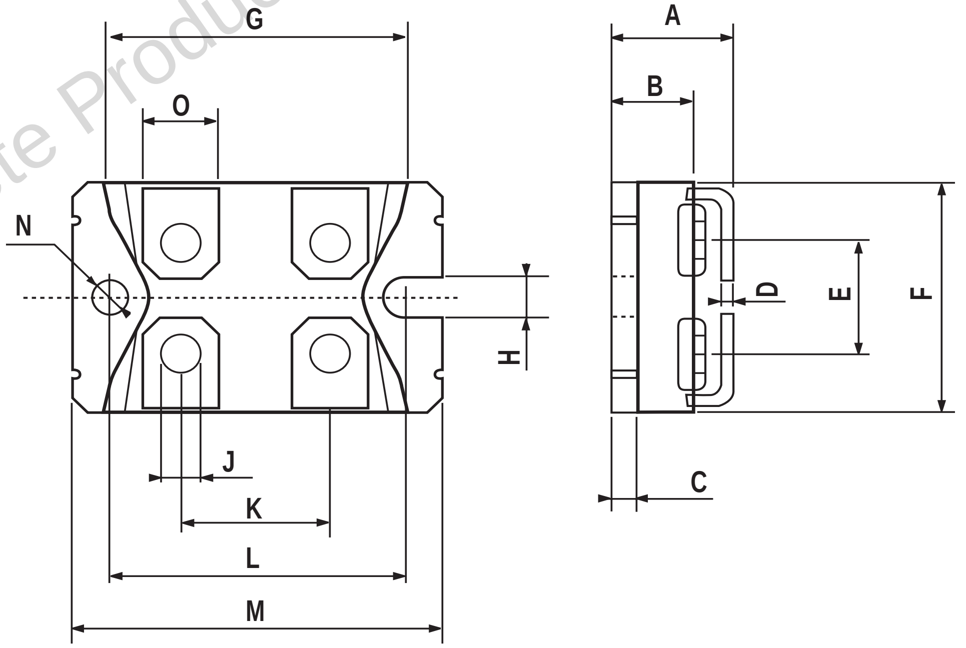


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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